

CORRECTION

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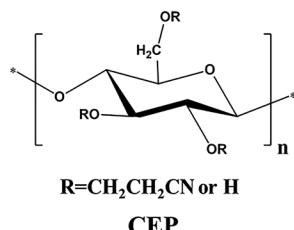
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Correction: Raw product of rare-earth ore works as a high-*k* gate insulator for low-voltage operable organic field-effect transistors

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 Correction for 'Raw product of rare-earth ore works as a high-*k* gate insulator for low-voltage operable organic field-effect transistors' by Xue-feng She *et al.*, *RSC Adv.*, 2016, **6**, 114593–114598.

The structure of the cyanoethylated pullulan polymer depicted in Fig. 1 was incorrect and the correct structure of the polymer unit is represented below:



The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.



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